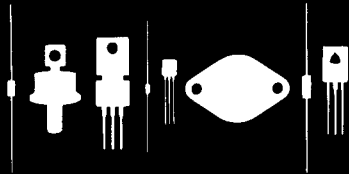


Central Semiconductor Corp.  
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 145 Adams Avenue  
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**1N485B**  
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 SILICON DIODE  
 JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N485B, 1N486B types are silicon planar diodes designed for low leakage applications.

MAXIMUM RATINGS ( $T_A = 25^{\circ}\text{C}$ )

|  | <u>SYMBOL</u>  | <u>1N485B</u> | <u>1N486B</u> | <u>UNITS</u>       |
|--|----------------|---------------|---------------|--------------------|
| Peak Repetitive Reverse Voltage                | $V_{RRM}$      | 200           | 250           | V                  |
| Peak Working Reverse Voltage                   | $V_{RWM}$      | 180           | 225           | V                  |
| Average Forward Current                        | $I_O$          | 200           | 200           | mA                 |
| Forward Steady-State Current                   | $I_F$          | 500           | 500           | mA                 |
| Peak Repetitive Forward Current                | $I_{FM}$       | 600           | 600           | mA                 |
| Peak Forward Surge Current (1.0 $\mu$ s pulse) | $I_{FSM}$      | 4.0           | 4.0           | A                  |
| Peak Forward Surge Current (1.0s pulse)        | $I_{FSM}$      | 1.0           | 1.0           | A                  |
| Power Dissipation                              | $P_D$          | 500           | 500           | mW                 |
| Operating and Storage<br>Junction Temperature  | $T_J, T_{stg}$ | -65 to +200   |               | $^{\circ}\text{C}$ |

ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}\text{C}$  unless otherwise noted)

| <u>SYMBOL</u> | <u>TEST CONDITIONS</u>                                   | <u>1N485B</u> |            | <u>1N486B</u> |            | <u>UNITS</u>  |
|---------------|--|---------------|------------|---------------|------------|---------------|
|               |  | <u>MIN</u>    | <u>MAX</u> | <u>MIN</u>    | <u>MAX</u> |               |
| $BV_R$        | $I_R = 100\mu\text{A}$                                   | 200           |            | 250           |            | V             |
| $I_R$         | $V_R = \text{Rated } V_{RWM}$                            |               | 25         |               | 50         | nA            |
| $I_R$         | $V_R = \text{Rated } V_{RWM}, T_A = 150^{\circ}\text{C}$ |               | 5.0        |               | 10         | $\mu\text{A}$ |
| $V_F$         | $I_F = 100\text{mA}$                                     |               | 1.0        |               | 1.0        | V             |

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